PCN Nu	mber:	20170206	5000		PCN Date:	Fe	eb.	14, 201	17
Title:	Datasheet fo	r INA199							
Custom	er Contact:	PCN Manage	<u>er</u>				De	pt:	Quality Services
Change	Туре:								
Ass	embly Site			Design				Wafer	Bump Site
Ass	embly Process			Data She	et			Wafer	Bump Material
	embly Material			Part num	ber change			Wafer	Bump Process
Med	hanical Specifi	cation		Test Site				Wafer	· Fab Site
Pac	king/Shipping/	Labeling		Test Proc	ess			Wafer	Fab Materials
								Wafer	Fab Process
			No	tificatio	on Details				
Descrip	tion of Chang	le:							
The follo	luct datasheet wing change h EXAS NSTRUMENTS	., .	•		ails.			DII 2000 D	INA199 EVISED FEBRUARY 2017
Changes	from Revision F (J	une 2016) to R	ovision	6	560	54090	3 – AP	RIL 2009-R	Page
Changes from Revision F (June 2016) to Revision G Page									
		-							differences 1
				•					
 Changed INA199Ax HBM value from ±4000 to ±2000 and changed INA199B1, INA199B2, and INA199B3 to INA199Bx and INA199Cx in second V_(ESD) section of ESD Ratings table 									

	INA199Bx and INA199Cx in second V _(ESD) section of ESD Ratings table	. 5
•	Changed maximum specification from 105 to 125 in T _A row of <i>Recommended Operating Conditions</i> table	
•	Changed all $T_A = -40^{\circ}C$ to $105^{\circ}C$ to $T_A = -40^{\circ}C$ to $125^{\circ}C$ in <i>Electrical Characteristics</i> table	. 7
•	Added version C to last row of V _{CM} parameter in <i>Electrical Characteristics</i> table	. 7
•	Added versions A and B to first Gain error parameter row, added second row	. 7

		·
•	Changed devices listed in test conditions of GBW parameter in <i>Electrical Characteristics</i> table to <i>INA199x1</i> , <i>INA199x2</i> , and <i>INA199x3</i> , respectively for the three rows	7
		÷.,
•	Changed maximum specification from 105 to 125 in Specified range parameter of Electrical Characteristics table	7
•	Changed 105°C to 125°C in last paragraph of Overview section	2

•	Changed INA199A2 and INA199B2 to INA199x2 and changed INA199A2 and INA199B2 to INA199x2 in last	
	paragraph of Input Filtering section	15
•	Changed listed products in table of Figure 22	15

The datasheet number will be changing.

Device Family	Change From:	Change To:
INA199	SBOS469F	SBOS469G

These changes may be reviewed at the datasheet links provided. <u>http://www.ti.com/product/INA199</u>

Reason for Change:

To accurately reflect the gain characteristics. Maximum Human Body Model (HBM) ESD stress voltage for version A is +/-2000.

Anticipated impact on Fit, Form, Function, Quality or Reliability (positive / negative):

No anticipated impact. This is a specification change announcement only. There are no changes to the actual device.

Changes to product identification resulting from this PCN:				
None.				
Product Affected:				
INA199A1DCKR	INA199A3DCKT	INA199B2RSWR	INA199C1RSWT	
INA199A1DCKT	INA199A3RSWR	INA199B2RSWT	INA199C2DCKR	
INA199A1RSWR	INA199A3RSWT	INA199B3DCKR	INA199C2DCKT	
INA199A1RSWT	INA199B1DCKR	INA199B3DCKT	INA199C2RSWR	
INA199A2DCKR	INA199B1DCKT	INA199B3RSWR	INA199C2RSWT	
INA199A2DCKT	INA199B1RSWR	INA199B3RSWT	INA199C3DCKR	
INA199A2RSWR	INA199B1RSWT	INA199C1DCKR	INA199C3DCKT	
INA199A2RSWT	INA199B2DCKR	INA199C1DCKT	INA199C3RSWR	
INA199A3DCKR	INA199B2DCKT	INA199C1RSWR	INA199C3RSWT	

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

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